1. Scope :

This specification applies to P/N silicon zener diode chips,
Device NO. SD-11260G

2. Structure :

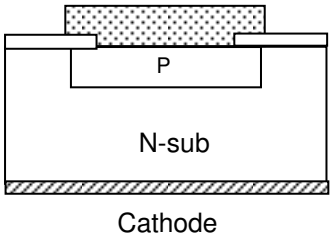
2-1. Planar type : P/N Diode
2-2. Electrodes :
Top side : Gold pad.
Back side : Gold layer.

3. Size :

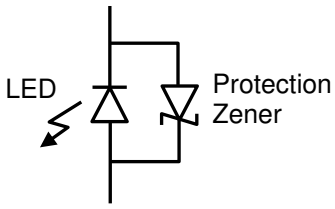
3-1. ※Chip size : 11.8 mils x 11.8 mils (0.300 mm x 0.300 mm).
3-2. Chip thickness : 6.0 ± 1.0 mils (0.150 ± 0.025 mm).
3-3. Active area : 6.3 mils x 6.3 mils (0.160 mm x 0.160 mm).
3-4. Bonding pad : 8.7 mils x 8.7 mils (0.220 mm x 0.220 mm).
3-5. Pattern drawing : Refer to the attached drawing.
※Including scribing line. The chip size is about $(0.275\pm0.015)^2 mm^2$ after dicing.

4. Electrical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I_R	V_R=4V Ee=0mW/cm²			100	nA
		V_R=5V Ee=0mW/cm²			0.5	μA
Zener Voltage	Vz	I_Z=5mA Ee=0mW/cm²	5.8		6.8	V
Forward Voltage	Vf	I_F=20mA Ee=0mW/cm²			1.2	



Anode

Cathode

Equivalent Circuit